

## 1700V N-Channel Depletion-Mode Power MOSFET

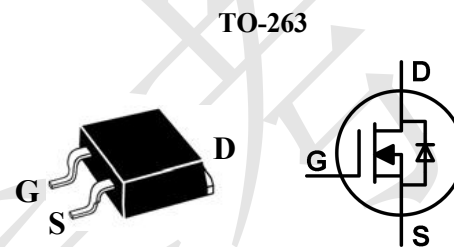
### General Features

- Depletion Mode (Normally On)
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- High Power Density
- RoHS Compliant
- Halogen-free Available
- Space Savings

$BV_{DSX}$	$R_{DS(ON)} (Max.)$	$I_{DSS(Min)}$
<b>1700V</b>	<b>20Ω</b>	<b>1.0A</b>

### Applications

- Suppressing Surge Current
- Start-up Circuits
- Converters
- Synchronous Rectification
- Audio Amplifiers
- Constant Current Source
- Ramp Generators
- Current Regulators
- Protection Circuits
- Active Loads



### Ordering Information

Part Number	Package	Marking	Remark
DMB13C170A	TO-263	13C170A	Halogen Free

### Absolute Maximum Ratings

$T_C=25^{\circ}C$  unless otherwise specified

Symbol	Parameter	DMB13C170A	Unit
$V_{DSX}$	Drain-to-Source Voltage <sup>[1]</sup>	1700	V
$V_{DGX}$	Drain-to-Gate Voltage <sup>[1]</sup>	1700	V
$P_D$	Power Dissipation	560	W
	Derating Factor above 25°C	560	W/°C
$V_{GS}$	Gate-to-Source Voltage	±20	V
$T_L$	Soldering Temperature	300	°C
	Distance of 1.6mm from case for 10 seconds		
$T_J$ and $T_{STG}$	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.